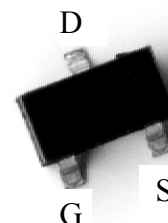


20V N-Channel Enhancement Mode MOSFET

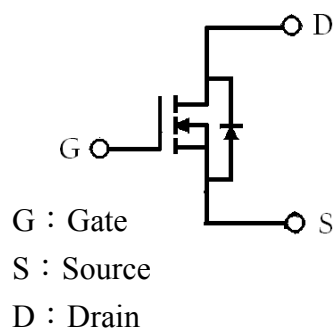
Features:

- Simple drive requirement
- Small package outline
- Capable of 2.5V gate drive
- Pb-free lead plating and halogen-free package

SOT-23



BV_{DSS}	20V
$I_D@V_{GS}=4.5V, T_A=25^\circ C$	3.6A
$R_{DS(on)}@V_{GS}=4.5V, I_D=3.6A$	29m Ω (typ.)
$R_{DS(on)}@V_{GS}=2.5V, I_D=3.1A$	39m Ω (typ.)



Ordering Information

Device	Package	Shipping
K2300	SOT-23 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±12	V
Continuous Drain Current @ V _{GS} =4.5V, T _A =25°C (Note 3)	I _D	3.6	A
Continuous Drain Current @ V _{GS} =4.5V, T _A =70°C (Note 3)		2.9	A
Pulsed Drain Current (Notes 1, 2)	I _{DM}	10	A
Maximum Power Dissipation@ T _A =25°C	P _D	1.38 (Note 3)	W
Linear Derating Factor		0.01	W/°C
Operating Junction and Storage Temperature	T _j , T _{stg}	-55~+150	°C

Note : 1. Pulse width limited by maximum junction temperature.

2. Pulse width ≤ 300μs, duty cycle ≤ 2%.

3. Surface mounted on 1 in² copper pad of FR-4 board, t ≤ 5s; 270°C/W when mounted on minimum copper pad.

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance, Junction-to-Ambient, max	R _{θJA}	90	°C/W
Thermal Resistance, Junction-to-Case, max	R _{θJC}	80	°C/W

Note : Surface mounted on 1 in² copper pad of FR-4 board, t ≤ 5s; 270°C/W when mounted on minimum copper pad.

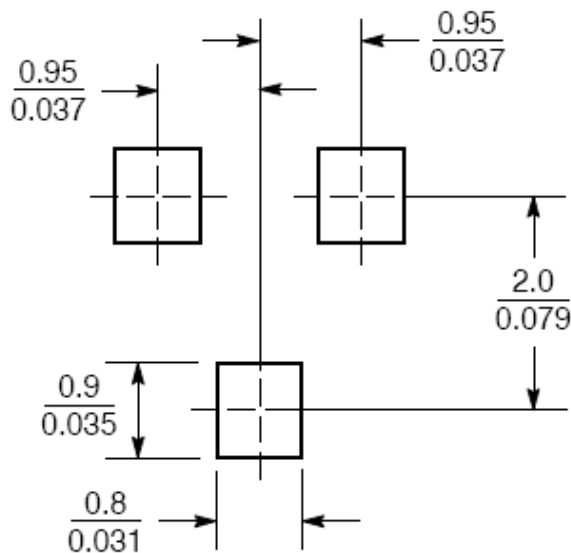
Electrical Characteristics (Tj=25°C, unless otherwise noted)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	20	-	-	V	V _{GS} =0, I _D =250μA
ΔBV _{DSS} /ΔT _j	-	0.1	-	V/°C	Reference to 25°C, I _D =1mA
V _{GS(th)}	0.5	0.7	1.2	V	V _{DS} =V _{GS} , I _D =250μA
I _{GSS}	-	-	±100	nA	V _{GS} =±12V, V _{DS} =0
I _{DSS}	-	-	1	μA	V _{DS} =20V, V _{GS} =0
	-	-	10	μA	V _{DS} =20V, V _{GS} =0 (T _j =70°C)
*R _{DS(ON)}	-	29	55	mΩ	I _D =3.6A, V _{GS} =4.5V
	-	39	70		I _D =3.1A, V _{GS} =2.5V
*G _{FS}	-	7.5	-	S	V _{DS} =5V, I _D =3.6A
Dynamic					
C _{iss}	-	440	-	pF	V _{DS} =10V, V _{GS} =0, f=1MHz
C _{oss}	-	61	-		
C _{rss}	-	59	-		
t _{d(ON)}	-	4.5	-	ns	V _{DS} =10V, I _D =3.6A, V _{GS} =5V R _G =6Ω, R _D =2.8Ω
t _r	-	7.4	-		
t _{d(OFF)}	-	19	-		
t _f	-	7.2	-		

Qg	-	4.4	-	nC	V _{DS} =10V, I _D =3.6A, V _{GS} =4.5V
Qgs	-	0.7	-		
Qgd	-	1.7	-		
Source-Drain Diode					
*V _{SD}	-	0.8	1.2	V	V _{GS} =0V, I _S =1.6A
I _S	-	-	1	A	V _D =V _G =0V, V _S =1.2V
I _{SM}	-	-	10		

*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

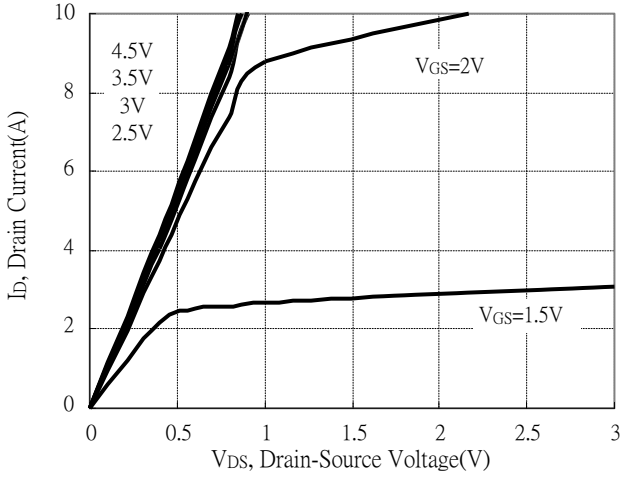
Recommended Soldering Footprint



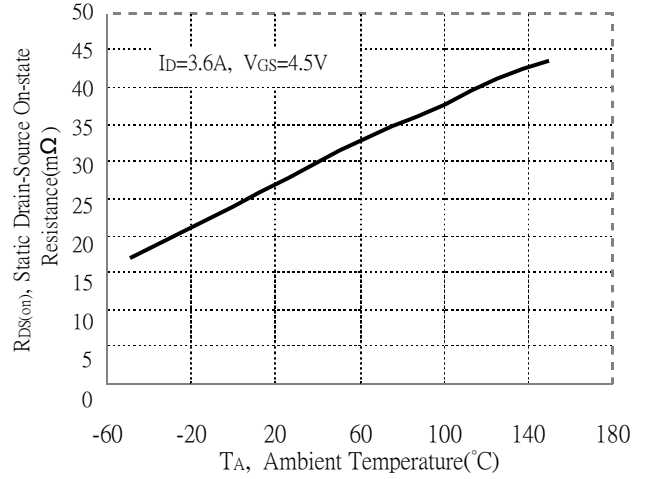
Unit : $\frac{\text{mm}}{\text{inches}}$

Typical Characteristics

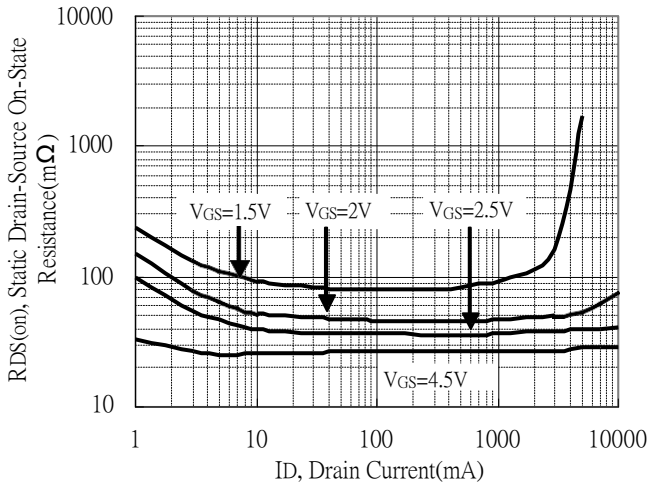
Typical Output Characteristics



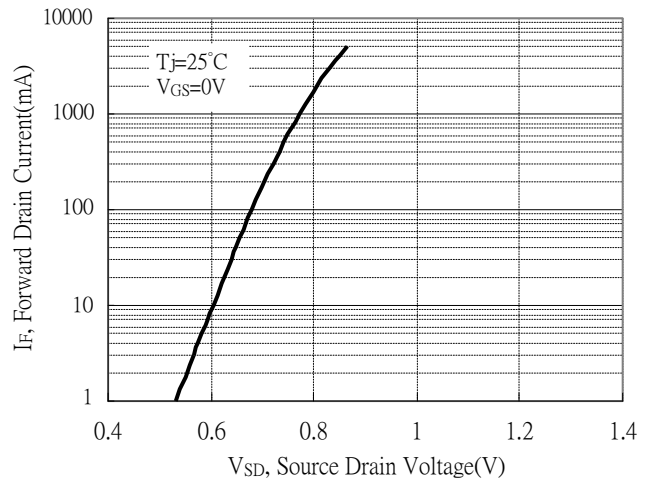
Static Drain-Source On-resistance vs Ambient Temperature



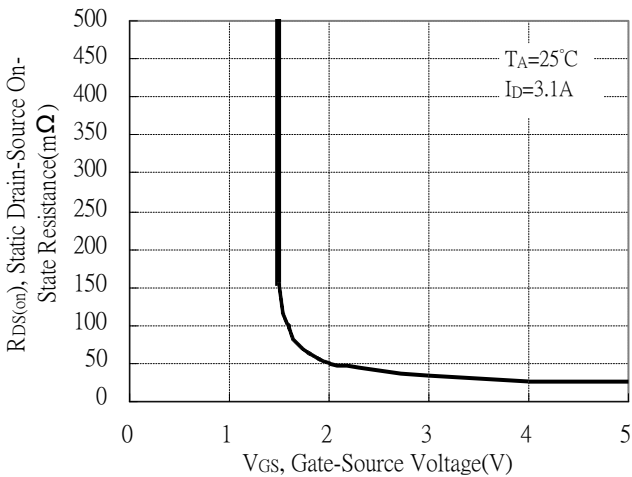
Static Drain-Source On-State resistance vs Drain Current



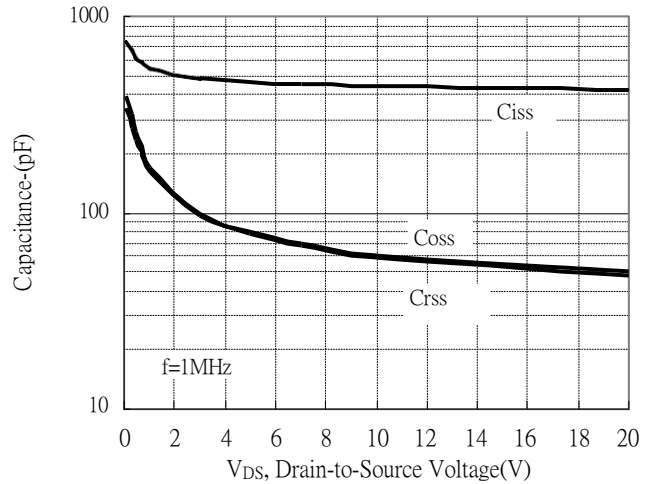
Forward Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

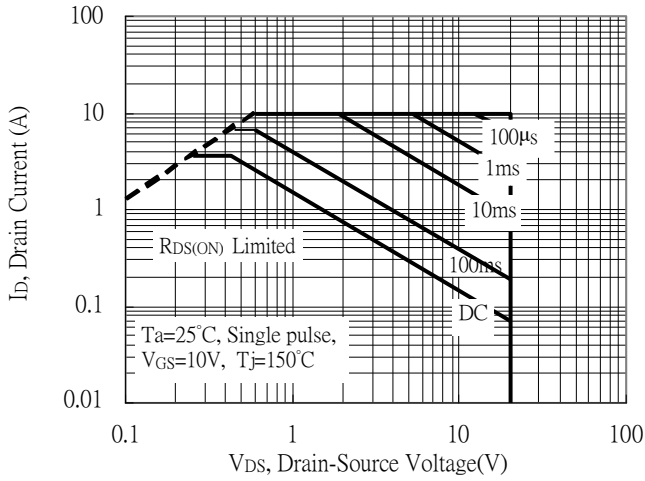


Capacitance vs Reverse Voltage

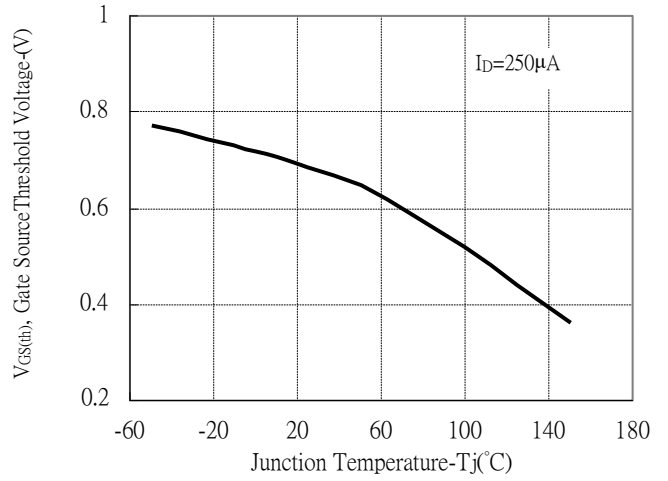


Typical Characteristics(Cont.)

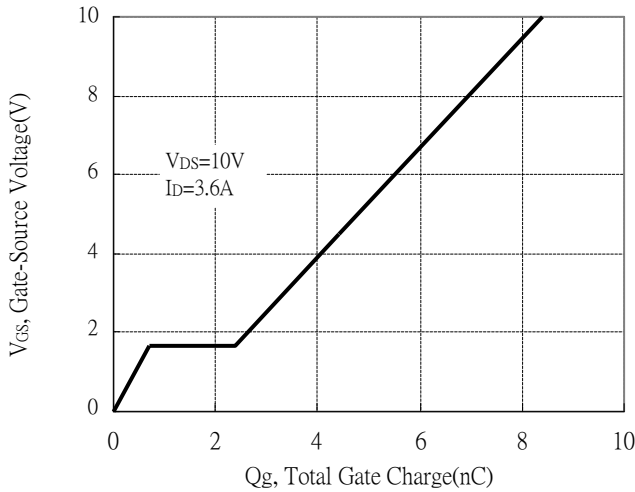
Maximum Safe Operating Area



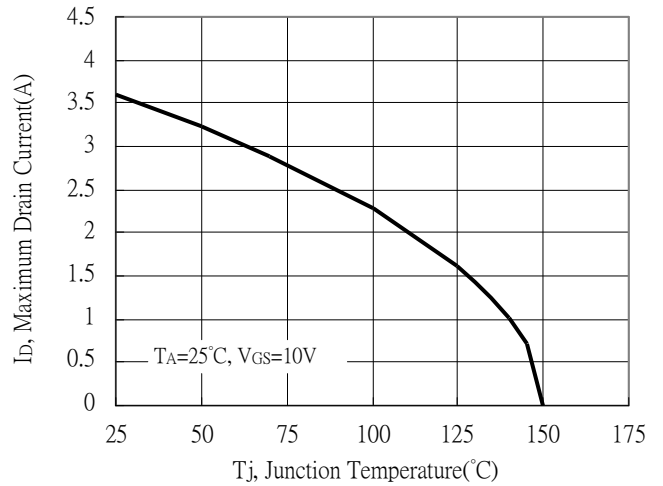
Gate Threshold Voltage vs Ambient Temperature



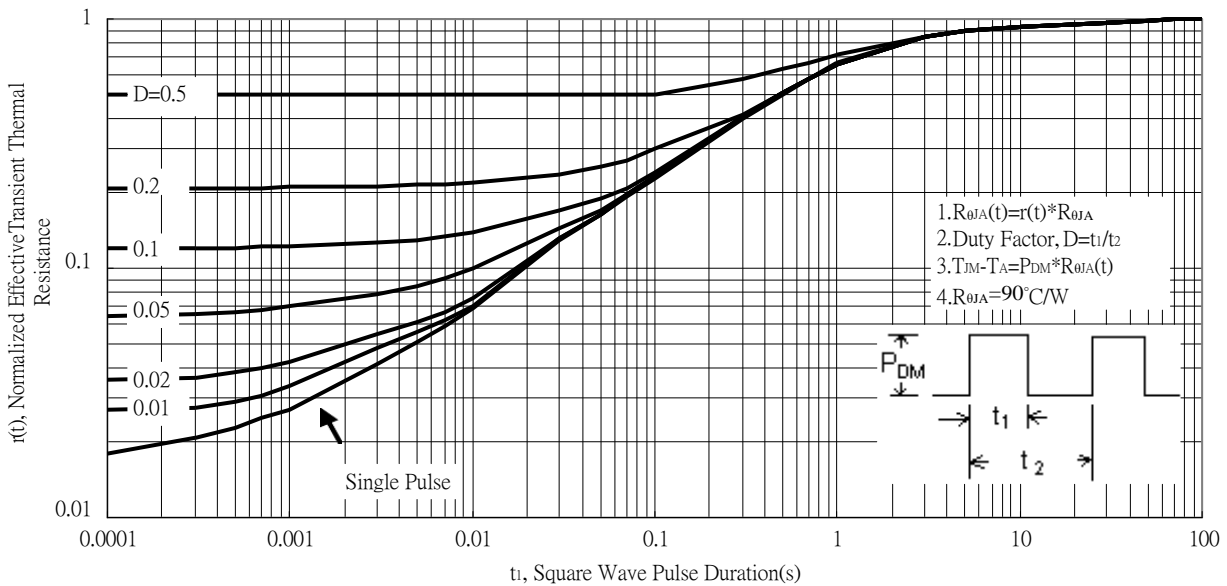
Gate Charge Characteristics



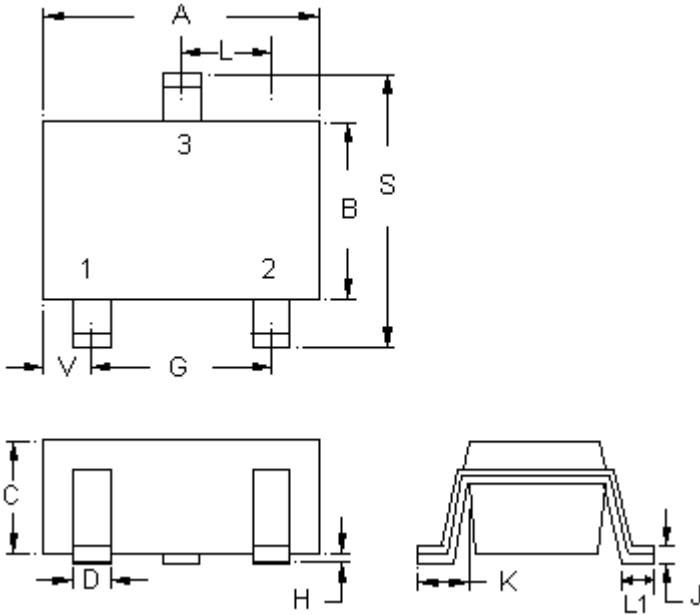
Maximum Drain Current vs Junction Temperature



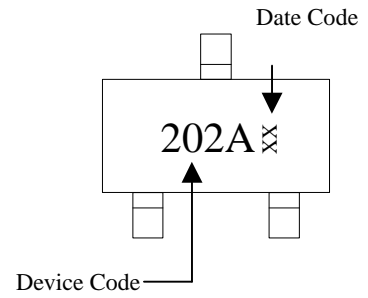
Transient Thermal Response Curves



SOT-23 Dimension



Marking:



3-Lead SOT-23 Plastic
 Surface Mounted Package
 Package Code: N3

Style: Pin 1.Gate 2.Source 3.Drain

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0032	0.0079	0.08	0.20
B	0.0472	0.0669	1.20	1.70	K	0.0118	0.0266	0.30	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1161	2.10	2.95
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0000	0.0040	0.00	0.10	L1	0.0118	0.0197	0.30	0.50